NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI UTV200** is Designed for Class A. UHF Television Applications up to 860 MHz.

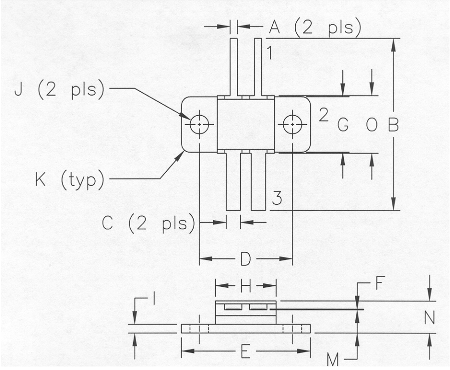
FEATURES INCLUDE:

- Internal Input Matching
- Gold Metalization
- Emitter Ballasting

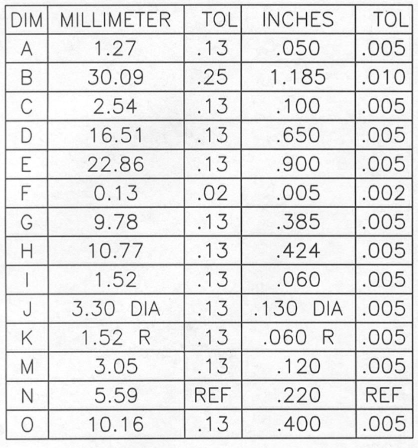
MAXIMUM RATINGS

I_C	4.5 A
V_{CE}	28 V
P_{DISS}	80 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.2 °C/W

PACKAGE STYLE .420 4L FLG.



1 = COLLECTOR 2 = EMITTER
3 = BASE



DIM	MILLIMETER	TOL	INCHES	TOL
A	1.27	.13	.050	.005
B	30.09	.25	1.185	.010
C	2.54	.13	.100	.005
D	16.51	.13	.650	.005
E	22.86	.13	.900	.005
F	0.13	.02	.005	.002
G	9.78	.13	.385	.005
H	10.77	.13	.424	.005
I	1.52	.13	.060	.005
J	3.30 DIA	.13	.130 DIA	.005
K	1.52 R	.13	.060 R	.005
M	3.05	.13	.120	.005
N	5.59	REF	.220	REF
O	10.16	.13	.400	.005

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 40 mA	28			V
BV_{CES}	I_C = 20 mA	50			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CBO}	V_{CB} = 30 V			50	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	10		150	---
C_{ob}	V_{CB} = 26 V f = 1.0 MHz			36	pF
P_G VSRW	V_{CE} = 26 V P_{OUT} = 20 W f = 470 - 860 MHz	8.5	9.5	 3:1	dB ---